

MITSUBISHI TRANSISTOR MODULES

QM15TB-2HB

MEDIUM POWER SWITCHING USE
INSULATED TYPE

QM15TB-2HB



- **IC** Collector current **15A**
- **V_{CEX}** Collector-emitter voltage **1000V**
- **h_{FE}** DC current gain **250**
- **Insulated Type**
- **UL Recognized**

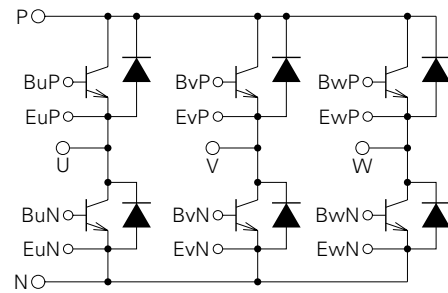
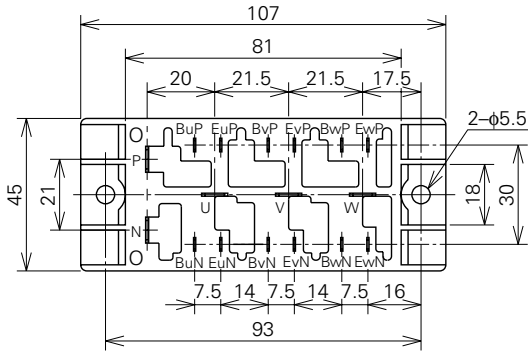
Yellow Card No. E80276 (N)
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APPLICATION

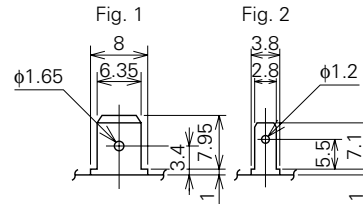
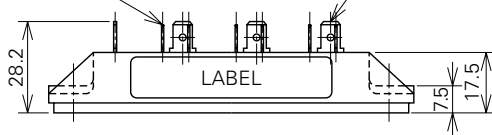
Inverters, Servo drives, DC motor controllers, NC equipment, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Tab#110, t=0.5 (Fig. 2) Tab#250, t=0.8 (Fig. 1)



Note: All Transistor Units are 3-Stage Darlington.

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INSULATED TYPE**

ABSOLUTE MAXIMUM RATINGS (T_j=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VCEX (SUS)	Collector-emitter voltage	I _C =1A, V _{EB} =2V	1000	V
VCEX	Collector-emitter voltage	V _{EB} =2V	1000	V
VCBO	Collector-base voltage	Emitter open	1000	V
VEBO	Emitter-base voltage	Collector open	7	V
I _C	Collector current	DC	15	A
-I _C	Collector reverse current	DC (forward diode current)	15	A
P _C	Collector dissipation	T _C =25°C	150	W
I _B	Base current	DC	1	A
-I _{CSM}	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	150	A
T _j	Junction temperature		-40~+150	°C
T _{stg}	Storage temperature		-40~+125	°C
V _{iso}	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Mounting screw M5	1.47~1.96	N·m
—	Weight	Typical value	15~20	kg·cm
—	Weight	Typical value	230	g

ELECTRICAL CHARACTERISTICS (T_j=25°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _C EX	Collector cutoff current	V _{CE} =1000V, V _{EB} =2V	—	—	1.0	mA
I _C BO	Collector cutoff current	V _{CB} =1000V, Emitter open	—	—	1.0	mA
I _E BO	Emitter cutoff current	V _{EB} =7V	—	—	50	mA
V _{CE} (sat)	Collector-emitter saturation voltage	I _C =15A, I _B =60mA	—	—	3.0	V
V _{BE} (sat)	Base-emitter saturation voltage		—	—	3.5	V
-V _{CEO}	Collector-emitter reverse voltage	-I _C =15A (diode forward voltage)	—	—	1.8	V
h _{FE}	DC current gain	I _C =15A, V _{CE} =3.0V	250	—	—	—
t _{on}	Switching time	V _{CC} =600V, I _C =15A, I _{B1} =90mA, I _{B2} =-0.3A	—	—	2.0	μs
t _s			—	—	10	μs
t _f			—	—	3.0	μs
R _{th} (j-c) Q	Thermal resistance (junction to case)	Transistor part (per 1/6 module)	—	—	0.8	°C/W
R _{th} (j-c) R		Diode part (per 1/6 module)	—	—	2.0	°C/W
R _{th} (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied (per 1/6 module)	—	—	0.35	°C/W